

General Description

The WSF3089 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSF3089 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline

Absolute Maximum Ratings

- 100% EAS Guaranteed
- Green Device Available

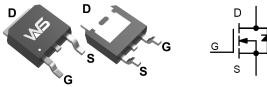
Product Summery

BVDSS	RDSON	ID
30V	4.5mΩ	72A

Applications

- Synchronous Buck Converter
- DC-DC Power System
- Load Switch

TO-252 Pin Configuration





Symbol Rating Units **Parameter** V V_{DS} Drain-Source Voltage 30 ± 20 V_{GS} Gate-Source Voltage V Continuous Drain Current,@TC=25°C¹ 72 А I_D Continuous Drain Current, @TC=100°C1 46 А Pulsed Drain Current² 200 А I_{DM} EAS Single Pulse Avalanche Energy³ 80 mJ \mathbf{P}_{D} W Total Power Dissipation @TC=25°C⁴ 50 TSTG °C Storage Temperature Range -55 to 150 $T_{\rm J}$ **Operating Junction Temperature Range** -55 to 150 °C

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient (Steady State) ¹		62	°C/W
R _{0JA}	Thermal Resistance Junction-Ambient ¹ (t ≤10s)		31	°C/W
R _{eJC}	Thermal Resistance Junction-Case ¹		2.5	°C/W



N-Ch MOSFET

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
$\triangle BV_{DSS} / \triangle T_J$	BVDSS Temperature Coefficient	Reference to 25 $^\circ\!\!{\rm C}$, I_D = 1mA		0.028		V/℃
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =30A		4.5	6.2	mΩ
		V _{GS} =4.5V , I _D =20A		7.0	9.2	
V _{GS(th)}	Gate Threshold Voltage	—V _{GS} =V _{DS} , I _D =250uA	1.1	1.5	2.5	V
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient			-6.16		mV/℃
	Drain-Source Leakage Current	V_{DS} =24V , V_{GS} =0V , T_J =25 $^\circ \mathrm{C}$			1	uA
I _{DSS}		V _{DS} =24V , V _{GS} =0V , T _J =55℃			5	
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm20V$, $V_{DS}=0V$			±100	nA
Qg	Total Gate Charge (4.5V)	V _{DS} =15V , V _{GS} =10V , I _D =30A		35		nC
Q _{gs}	Gate-Source Charge			6.8		
Q _{gd}	Gate-Drain Charge			7.5		
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V , V _{GS} =10V , R _G =6Ω I _D =15A		11		
Tr	Rise Time			15		ns
T _{d(off)}	Turn-Off Delay Time			37.3		
T _f	Fall Time			10.6		
Ciss	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		1800		
C _{oss}	Output Capacitance			220		pF
C _{rss}	Reverse Transfer Capacitance			178		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,6}				72	А
I _{SM}	Pulsed Source Current ^{2,6}	$V_G = V_D = 0V$, Force Current			200	А
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25℃			1.3	V
t _{rr}	Reverse Recovery Time			10		nS
Qrr	Reverse Recovery Charge	IF=20A , dI/dt=100A/µs , Tյ=25℃		2.5		nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.

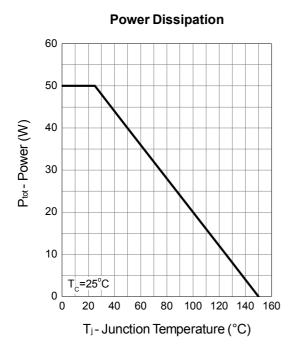
- 2. The data tested by pulsed , pulse width ≤ 300 us , duty cycle $\leq 2\%$ 3. The EAS data shows Max. rating . The test condition is V_{DD}=15V,V_{GS}=10V,L=0.5mH,I_{AS}=18A
- $4. The power dissipation is limited by 175 <math display="inline">^\circ\!\!\!\mathrm{C}$ junction temperature
- 5. The Min. value is 100% EAS tested guarantee.

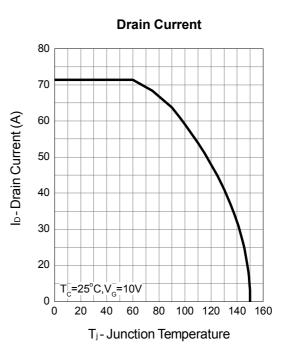
6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



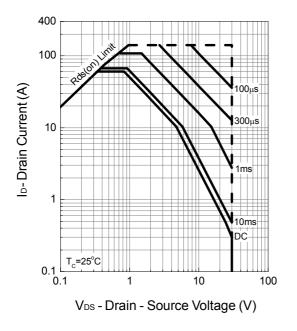
N-Ch MOSFET

Typical Operating Characteristics

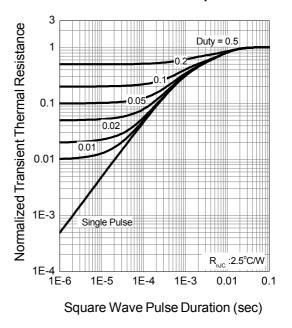




Safe Operation Area



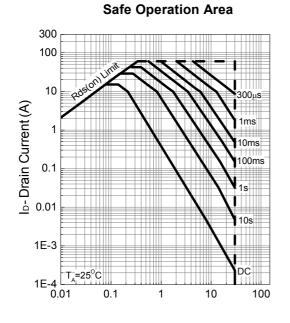
Thermal Transient Impedance





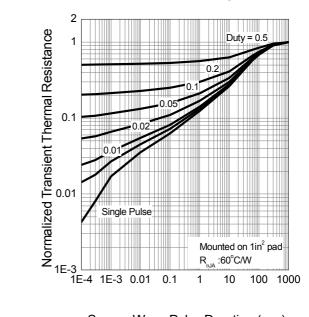
N-Ch MOSFET

Typical Operating Characteristics

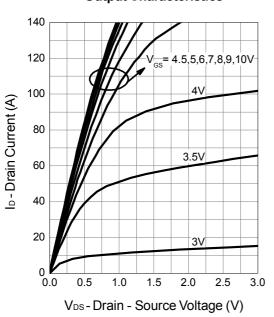


V_{DS} - Drain - Source Voltage (V)

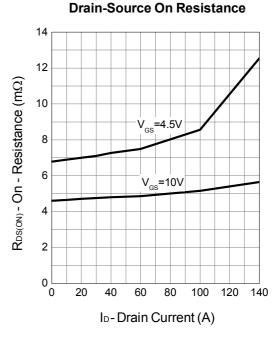
Thermal Transient Impedance



Square Wave Pulse Duration (sec)



Output Characteristics

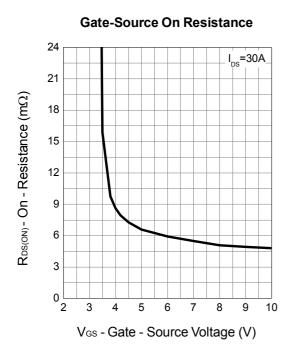


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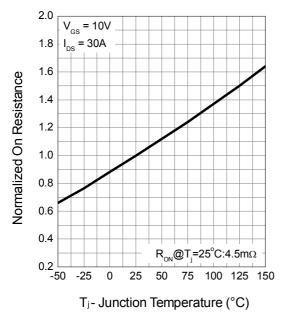


N-Ch MOSFET

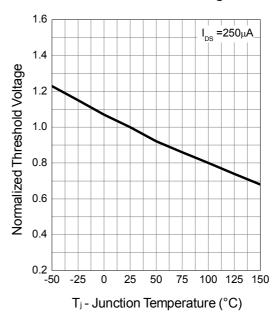
Typical Operating Characteristics



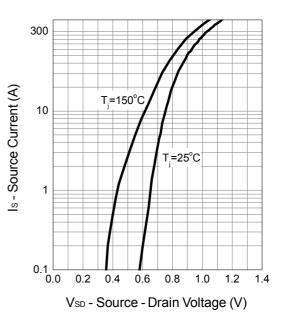
Drain-Source On Resistance



Gate Threshold Voltage



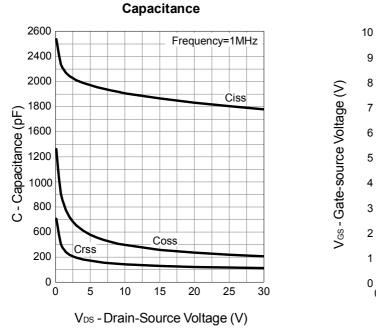
Source-Drain Diode Forward

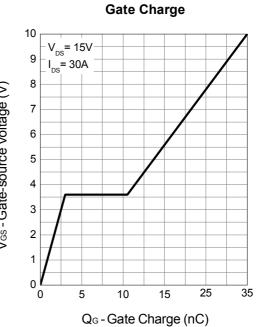




N-Ch MOSFET

Typical Operating Characteristics







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